CLAIM AMENDMENTS

1. (Currently Amended) A semiconductor laser device comprising~~:~~ a dielectric multilayer film with a reflectance of at least 40%~~ or more, formed~~ on at least one of optical exit faces of a laser chip~~;~~, wherein the dielectric multilayer film includes a~~ dielectric~~ film of tantalum oxide.

2. (Currently Amended) The semiconductor laser device according to Claim 1, wherein the dielectric multilayer film includes a~~ dielectric~~ film of aluminum oxide and the ~~dielectric~~ film of tantalum oxide.

3. (Currently Amended) The semiconductor laser device according to Claim 1, wherein the dielectric multilayer film includes a~~ dielectric~~ film of aluminum oxide~~ for a film~~ in contact with the laser chip, and~~ further includes~~ a~~ dielectric~~ film of silicon oxide and the ~~dielectric~~ film of tantalum oxide.

4. (Currently Amended) The semiconductor laser device according to Claim 2, wherein the dielectric multilayer film is configured of a total of nine layers of, in sequence from the side in contact with the laser chip, an aluminum oxide film, a tantalum oxide film, an aluminum oxide film, a tantalum oxide film, an aluminum oxide film, a tantalum oxide film, an aluminum oxide film, a tantalum oxide film, and an aluminum oxide film.

5. (Currently Amended) The semiconductor laser device according to Claim 4, wherein each~~ thickness~~ of the first to eighth layers, from the side in contact with the laser chip,~~ in the dielectric multilayer film is~~ has a thickness equivalent to $\lambda/4$ in terms of optical length~~ using~~, at an oscillation wavelength λ of the laser chip, and~~ thickness of~~ the ninth layer ~~is~~ has a thickness equivalent to $\lambda/2$ in terms of optical length.

6. (Currently Amended) The semiconductor laser device according to Claim 3, wherein the dielectric multilayer film is configured of a total of eight layers of, in sequence from the side in contact with the laser chip, an aluminum oxide film, a silicon film, a tantalum oxide film, a silicon film, a tantalum oxide film, a silicon film, a tantalum oxide film, and a silicon film.

7. (Currently Amended) The semiconductor laser device according to Claim 6, wherein ~~thickness of~~ the first layer, from the side in contact with the laser chip, ~~in the dielectric multilayer film is~~ has a thickness equivalent to $\lambda/2$ in terms of optical length ~~using~~, at an oscillation wavelength λ of the laser chip, and each ~~thickness~~ of the second to seventh layers ~~is~~ has a thickness equivalent to $\lambda/4$ in terms of optical length, and ~~thickness of~~ the eighth layer ~~is~~ has a thickness equivalent to $\lambda/2$ in terms of optical length.